

PROCESS FOR PREPARING A THIN FILM OF FERROELECTRIC MATERIAL**ABSTRACT**

The invention relates to a method for preparing a thin film (3) of ferroelectric material, the method comprising a step of providing the thin film (3), the thin film (3) exposing a first free face (8). The method also comprises a step of thinning by ion etching, and defined by etching parameters. According to the invention, the etching parameters are chosen so that the free face (8) of the thin film (3) has a roughness which does not exceed a threshold value at the end of the thinning step.

Fig. 3